

ABSTRACT OF THE DISCLOSURE

The present invention includes an angle adjuster that alters the path of an ion beam prior to contacting a target wafer. The path is altered according to a target position on the wafer in one or two dimensions in order to compensate for angle variations inherent in batch ion implantation system. The angle adjuster comprises one or more bending elements that controllably alter the path of the ion beam during ion implantation. As a result, the target wafer can be implanted with a substantially uniform implant angle.